

DESCRIPTION

Mitsubishi 2SC4154 is a super mini package resin sealed silicon NPN epitaxial type transistor. It is designed for low frequency voltage amplify application. Complementary with 2SA1602.

FEATURE

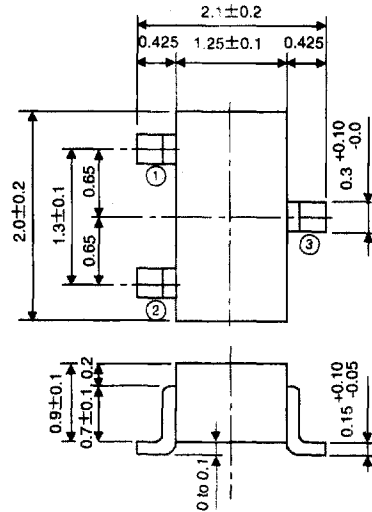
- Small collector to emitter saturation voltage
 $V_{CE(sat)}=0.3V \text{ max } (@I_C=100mA, I_B=10mA)$
- Excellent linearity of DC forward current gain
- Super mini package for easy mounting

APPLICATION

For hybrid IC, small type machine low frequency voltage amplify application.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

- ① : BASE
- ② : EMITTER
- ③ : COLLECTOR

EIAJ : SC-70

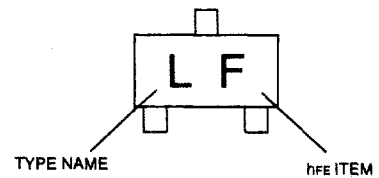
Note)

The dimension without tolerance represent central value.

MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V _{CB0}	Collector to Base voltage	50	V
V _{EB0}	Emitter to Base voltage	6	V
V _{CE0}	Collector to Emitter voltage	50	V
I _C	Collector current	200	mA
P _C	Collector dissipation(Ta=25°C)	150	mW
T _J	Junction temperature	+125	°C
T _{stg}	Storage temperature	-55 to +125	°C

MARKING



ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{(BR)CEO}	C to E break down voltage	I _C =100 μA, R _{BE} =∞	50			V
I _{CB0}	Collector cut off current	V _{CB} =50V, I _E =0			0.1	μA
I _{EB0}	Emitter cut off current	V _{EB} =6V, I _C =0			0.1	μA
h _{FE} *	DC forward current gain	V _{CE} =6V, I _C =1mA	150		800	—
h _{FE}	DC forward current gain	V _{CE} =6V, I _C =0.1mA	90			—
V _{CE(sat)}	C to E saturation voltage	I _C =100mA, I _B =10mA			0.3	V
f _T	Gain band width product	V _{CE} =6V, I _E =-10mA		200		MHz
C _{ob}	Collector output capacitance	V _{CB} =6V, I _E =0, f=1MHz		2.5		pF
NF	Noise figure	V _{CE} =6V, I _E =-0.1mA, f=1kHz, R _G =2kΩ			15	dB

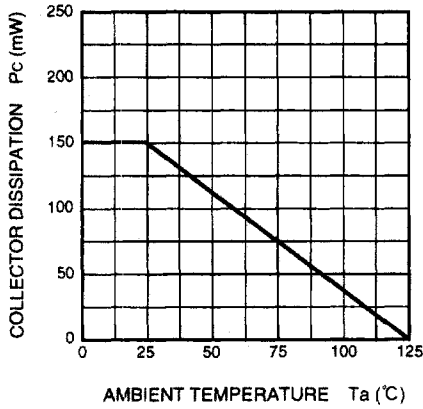
* : It shows h_{FE} classification in right table.

Item	E	F	G
h _{FE}	150 to 300	250 to 500	400 to 800
Marking	LE	LF	LG

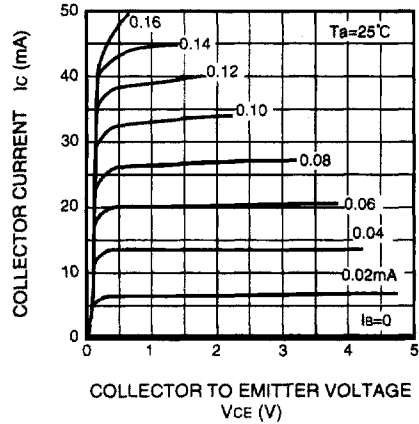
FOR LOW FREQUENCY AMPLIFY APPLICATION
SILICON NPN EPITAXIAL TYPE

TYPICAL CHARACTERISTICS

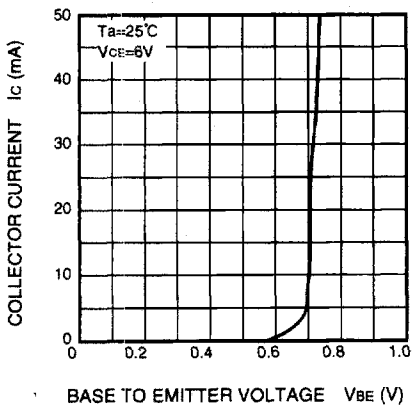
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



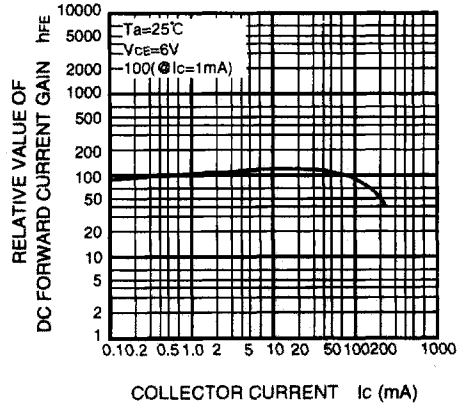
COMMON EMITTER OUTPUT



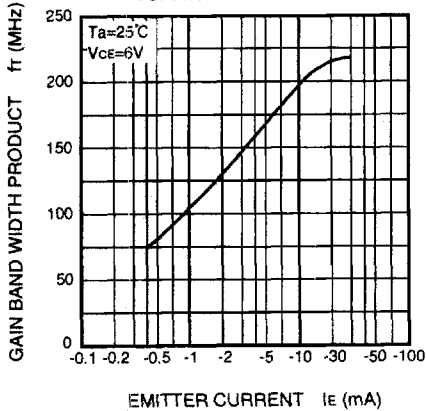
COMMON EMITTER TRANSFER



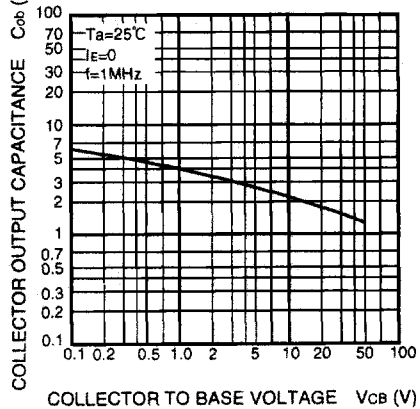
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



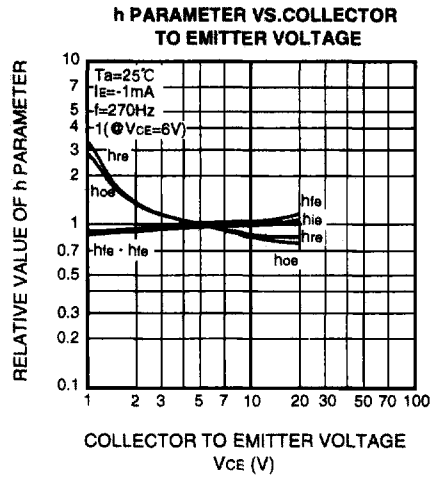
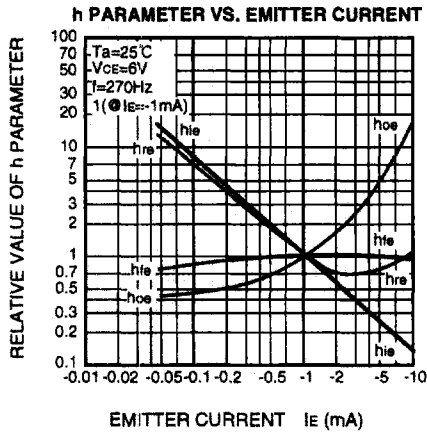
GAIN BAND WIDTH PRODUCT VS. EMITTER CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



FOR LOW FREQUENCY AMPLIFY APPLICATION
SILICON NPN EPITAXIAL TYPE



COMMON EMITTER h PARAMETER (TYPICAL VALUE)

Symbol	Parameter	Test conditions	Limits	Unit
h_{ie}	Closed loop small signal input impedance	$T_a=25^\circ\text{C}$	8.5	k Ω
h_{re}	Open loop small signal reverse voltage amplification factor	$V_{CE}=6\text{V}$	0.1	$\times 10^{-3}$
h_{fe}	Closed loop small signal forward current amplification factor	$I_E=-1\text{mA}$	300	—
h_{oe}	Open loop small signal output admittance	$f=270\text{Hz}$	5.5	μS